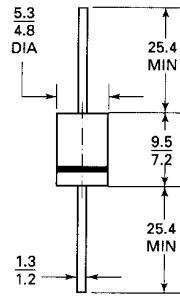


R30A...R30M FAST SILICON RECTIFIERS

FEATURES

- * Low forward voltage
- * High current capability
- * Low leakage current
- * High surge capability
- * Low cost

DO - 201AD



VOLTAGE RANGE

50 to 1000 Volts

CURRENT

3.0 Amperes

Dimensions in mm

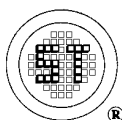
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

	R30A	R30B	R30D	R30G	R30J	R30K	R30M	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current .375". 9.5mm Lead Length at T _A = 60 °C	3.0							A
Peak Forward Surge Current 8.3 ms single half sine-wave	150							A
Maximum Forward Voltage at 3.0A Peak	1.3							V
Maximum Full Load Reverse Current, Full Cycle Average. .375", (9.5mm) Lead Length at T _A = 55 °C	50							μA
Maximum DC Reverse Current, at Rated DC Blocking Voltage	5							μA
Maximum Reverse Recovery Time (Note 1)	150	150	150	150	250	500	500	ns
Typical Junction Capacitance (Note 2)	65							pF
Operating and Storage Temperature Range	-65 to + 175							°C

NOTES:

1. Reverse Recovery Test Conditions: I_F = .5A, I_R = 1.0A, I_r = .25A
2. Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts



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Fig. 1—REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

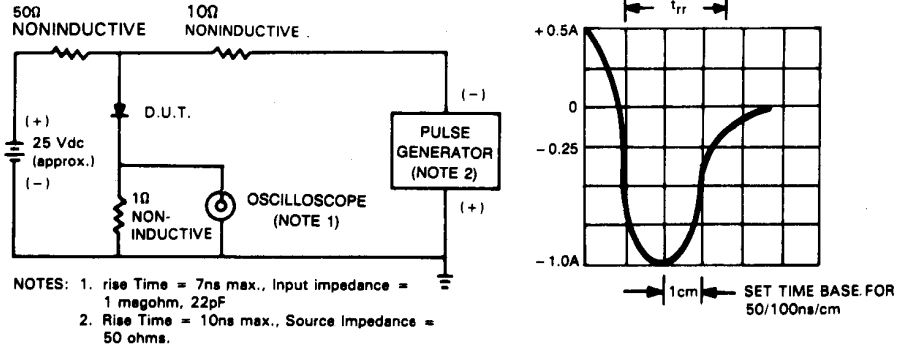


Fig. 2—FORWARD CURRENT DERATING CURVE

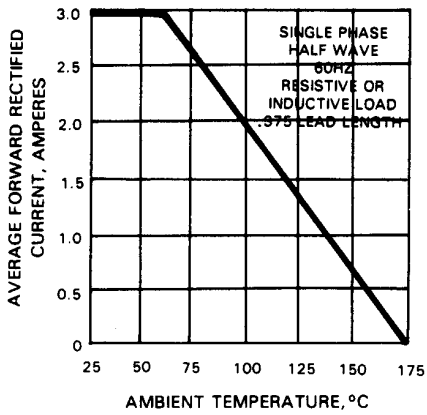
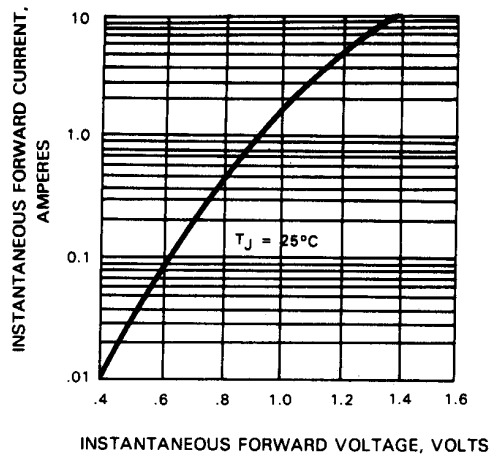


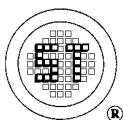
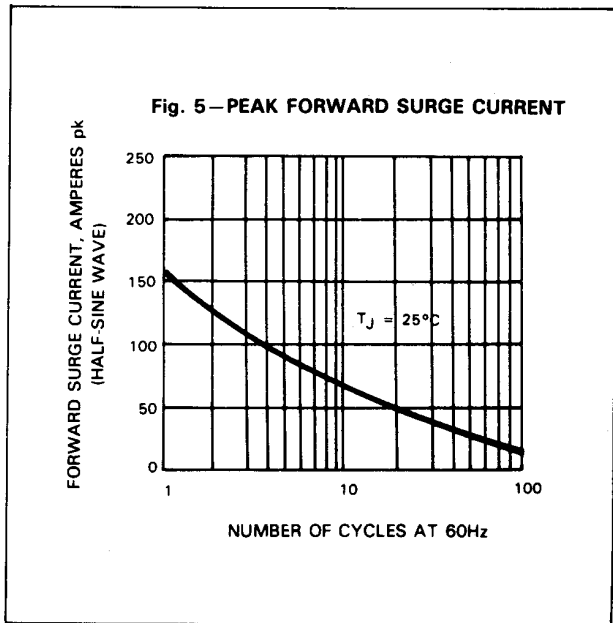
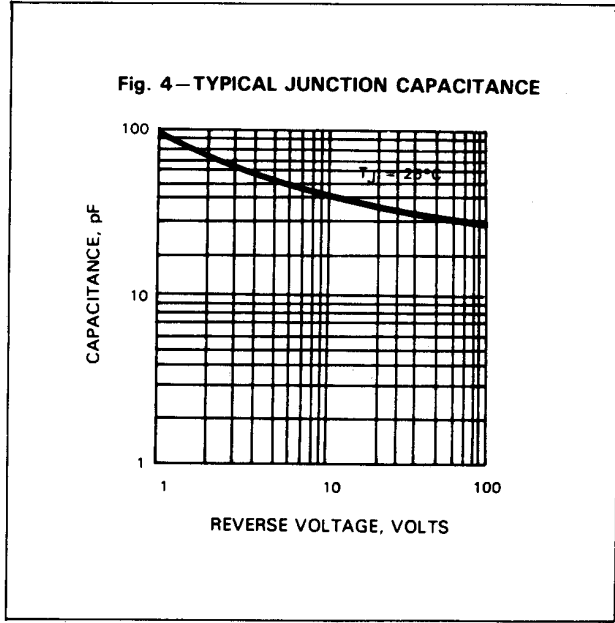
Fig. 3—TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS



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